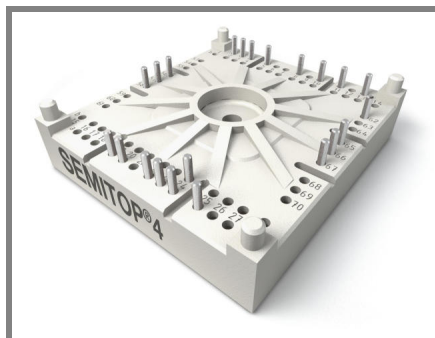


SK100GD066T



SEMITOP® 4

IGBT Module

SK100GD066T

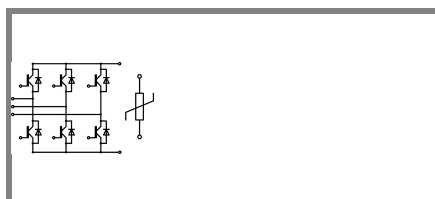
Preliminary Data

Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

Typical Applications*

- Inverter up to 22 kVA
- Typ. motor power 11 kW

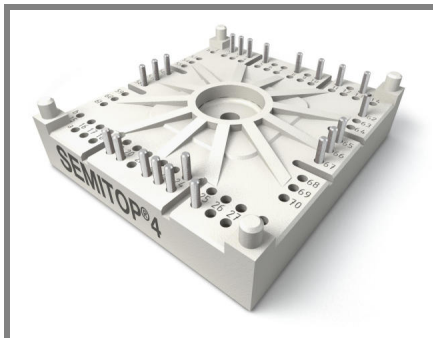


GD-T

Absolute Maximum Ratings		$T_s = 25\text{ °C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}	$T_j = 25\text{ °C}$	600	V
I_C	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	105
		$T_s = 70\text{ °C}$	85
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	200	A
V_{GES}		± 20	V
t_{psc}	$V_{CC} = 360\text{ V}$; $V_{GE} \leq 20\text{ V}$; $T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	6	μs
Inverse Diode			
I_F	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	99
		$T_s = 70\text{ °C}$	79
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	120	A
Module			
$I_{t(RMS)}$			A
T_{vj}		-40 ... +175	$^{\circ}\text{C}$
T_{stg}		-40 ... +125	$^{\circ}\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 1,6\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,005	mA
		$T_j = 125\text{ °C}$			mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = 20\text{ V}$	$T_j = 25\text{ °C}$		600	nA
		$T_j = 125\text{ °C}$			nA
V_{CE0}		$T_j = 25\text{ °C}$	0,9	1,1	V
		$T_j = 150\text{ °C}$	0,8	1	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	5,5	7,5	$\text{m}\Omega$
		$T_j = 150\text{ °C}$	8,5	10,5	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 100\text{ A}$, $V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,65	2,05	V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	6,1		nF
C_{oes}			0,38		nF
C_{res}			0,18		nF
$t_{d(on)}$	$R_{Gon} = 32\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 100\text{ A}$	144		ns
t_r			128		ns
E_{on}			7		mJ
$t_{d(off)}$	$R_{Goff} = 32\ \Omega$ $di/dt = 2575\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = -7/+15\text{ V}$	1040		ns
			91		ns
E_{off}			6		mJ
$R_{th(j-s)}$	per IGBT		0,65		K/W

SK100GD066T



SEMITOP® 4

IGBT Module

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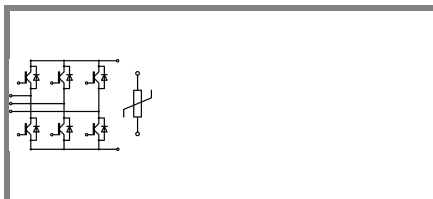
Preliminary Data

Features

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Typical Applications*

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GD-T

Characteristics

Symbol	Conditions	min.	typ.	max.	Units
Inverse Diode					
$V_F = V_{EC}$	$I_{Fnom} = 100 \text{ A}; V_{GE} = 0 \text{ V}$	$T_j = 25 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,3		V
		$T_j = 150 \text{ }^\circ\text{C}_{\text{chiplev.}}$	1,3		V
V_{F0}		$T_j = 25 \text{ }^\circ\text{C}$	0,95		V
		$T_j = 150 \text{ }^\circ\text{C}$	0,85		V
r_F		$T_j = 25 \text{ }^\circ\text{C}$	3,5		mΩ
		$T_j = 150 \text{ }^\circ\text{C}$	4,5		mΩ
I_{RRM}	$I_F = 100 \text{ A}$		60		A
Q_{rr}	$di/dt = 2575 \text{ A}/\mu\text{s}$		5,6		μC
E_{rr}	$V_{CC} = 300\text{V}$		1,7		mJ
$R_{th(j-s)D}$	per diode		0,8		K/W
M_s	to heat sink	2,5		2,75	Nm
w			60		g
Temperature sensor					
R_{100}	$T_s = 100 \text{ }^\circ\text{C} (R_{25} = 5\text{k}\Omega)$		493±5%		Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

